

direction where the cross section is elongated in the first direction and the length is longer than the width;

placing a substrate between said first and second electrodes;

etching a material over said substrate by said plasma;

changing a relative location of the substrate with the plasma in the second direction.

³³ 74. (New) The process according to claim ³² 73 wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

³⁴ 75. (New) The process according to claim ³² 73 wherein said etching gas comprises nitrogen fluoride.

F1
contd ³⁵ 76. (New) A process comprising the steps of:
providing first and electrodes opposed in parallel to each other in a reaction chamber,
said first electrode having a plurality of gas inlets arranged in a first direction;
introducing an ashing gas through said plurality of gas inlets into said reaction chamber;

generating a plasma of said ashing gas by applying a voltage between said first and second electrode wherein said plasma extends between the first electrode and the second electrode and a cross section of the plasma along planes of the first and second electrodes has a length along the first direction and a width along a second direction perpendicular to the first direction where the cross section is elongated in the first direction and the length is longer than the width;

placing a substrate between said first and second electrodes;

ashing a material over said substrate by said plasma;

changing a relative location of the substrate with the plasma in the second direction.

³⁶ 77. (New) The process according to claim ³⁵ 76 wherein a pressure in said reaction chamber is from 0.1 to 800 Torr.

³⁷
~~37~~ 78. (New) The process according to claim ~~76~~³⁵ wherein said material is a resist.

³⁸
~~38~~ 79. (New) The process according to claim ~~76~~³⁵ wherein said substrate is a glass substrate.

³⁹
~~39~~ 80. (New) A process comprising the steps of:

providing first and second electrodes opposed to each other in a reaction chamber,
said first electrode having at least one inlet having an opening elongated in a first direction;
introducing an etching gas through said at least one inlet into said reaction chamber;
generating a plasma of said etching gas by applying a voltage between said first and
second electrodes wherein at each said at least one inlet said plasma extends from the first
electrode toward the second electrode and at each said at least one inlet a cross section of the
plasma has a length along the first direction and a width along a second direction perpendicular
to the first direction and parallel to the electrodes where the length is longer than the width;
placing a substrate between said first and second electrodes;
etching a material over the substrate by the plasma of said etching gas; and
changing a relative location of the substrate with respect to the plasma in the second
direction during the etching.

⁴⁰
~~40~~ 81. (New) The process according to claim ~~80~~³⁹ wherein a pressure in said reaction
chamber is from 0.1 to 800 Torr.

⁴¹
~~41~~ 82. (New) The process according to claim ~~80~~³⁹ wherein said etching gas comprises
nitrogen fluoride.

⁴²
~~42~~ 83. (New) A process comprising the steps of:
providing first and second electrodes opposed to each other in a reaction chamber,
said first electrode having at least one inlet having an opening elongated in a first direction;
introducing an ashing gas through said at least one inlet into said reaction chamber;